

SOT-26



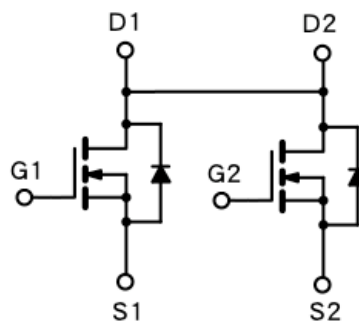
Pin Definition:

- | | |
|-----------|-------------|
| 1. Gate 1 | 6. Source 1 |
| 2. Drain | 5. Drain |
| 3. Gate 2 | 4. Source 2 |

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (m Ω)	I_D (A)
20	30 @ $V_{GS} = 4.5V$	6.0
	40 @ $V_{GS} = 2.5V$	5.2

Block Diagram



Dual N-Channel MOSFET

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

- Specially Designed for Li-on Battery Packs
- Battery Switch Application

Ordering Information

Part No.	Package	Packing
TSM9966DCX6 RF	SOT-26	3Kpcs / 7" Reel

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	6	A
Pulsed Drain Current	I_{DM}	30	A
Continuous Source Current (Diode Conduction) ^{a,b}	I_S	1.7	A
Maximum Power Dissipation	P_D	Ta = 25°C	1.6
		Ta = 75°C	1.1
Operating Junction Temperature	T_J	+150	°C
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R_{\theta_{JC}}$	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R_{\theta_{JA}}$	80	°C/W

Notes:

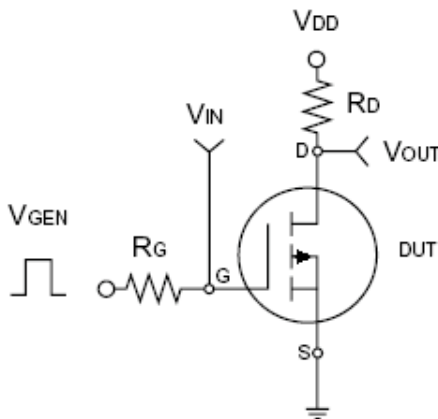
- Pulse width limited by the Maximum junction temperature
- Surface Mounted on FR4 Board, $t \leq 5$ sec.

Electrical Specifications (Ta = 25°C unless otherwise noted)

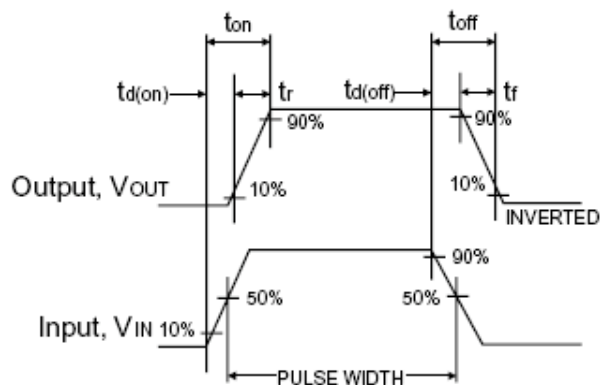
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250uA	BV _{DSS}	20	--	--	V
Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250uA	V _{GS(TH)}	0.6	--	--	V
Gate Body Leakage	V _{GS} = ±12V, V _{DS} = 0V	I _{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V _{DS} = 20V, V _{GS} = 0V	I _{DSS}	--	--	1.0	uA
On-State Drain Current	V _{DS} = 5V, V _{GS} = 4.5V	I _{D(ON)}	30	--	--	A
Drain-Source On-State Resistance	V _{GS} = 4.5V, I _D = 6.0A	R _{DS(ON)}	--	21	30	mΩ
	V _{GS} = 2.5V, I _D = 5.2A		--	30	40	
Forward Transconductance	V _{DS} = 10V, I _D = 6A	g _{fs}	--	30	--	S
Diode Forward Voltage	I _S = 1.7A, V _{GS} = 0V	V _{SD}	--	0.7	1.2	V
Dynamic^b						
Total Gate Charge	V _{DS} = 10V, I _D = 6A, V _{GS} = 4.5V	Q _g	--	5	7	nC
Gate-Source Charge		Q _{gs}	--	1	--	
Gate-Drain Charge		Q _{gd}	--	1.5	--	
Input Capacitance	V _{DS} = 8V, V _{GS} = 0V, f = 1.0MHz	C _{iss}	--	565	--	pF
Output Capacitance		C _{oss}	--	105	--	
Reverse Transfer Capacitance		C _{rss}	--	75	--	
Switching^c						
Turn-On Delay Time	V _{DD} = 10V, R _G = 6Ω, I _D = 1A, V _{GEN} = 4.5V,	t _{d(on)}	--	8	20	nS
Turn-On Rise Time		t _r	--	10	20	
Turn-Off Delay Time		t _{d(off)}	--	22	45	
Turn-Off Fall Time		t _f	--	6	15	

Notes:

- a. pulse test: PW ≤ 300μs, duty cycle ≤ 2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



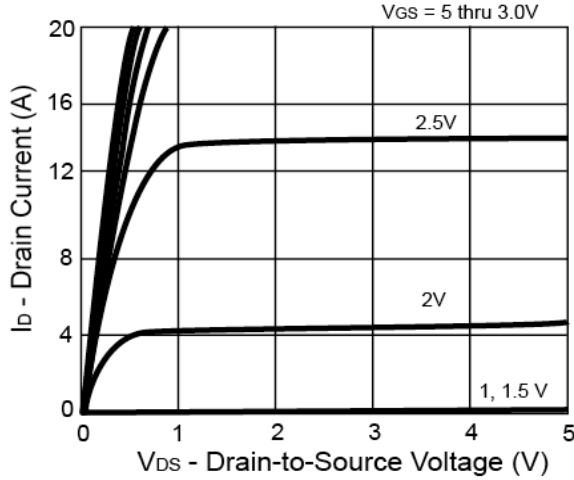
Switching Test Circuit



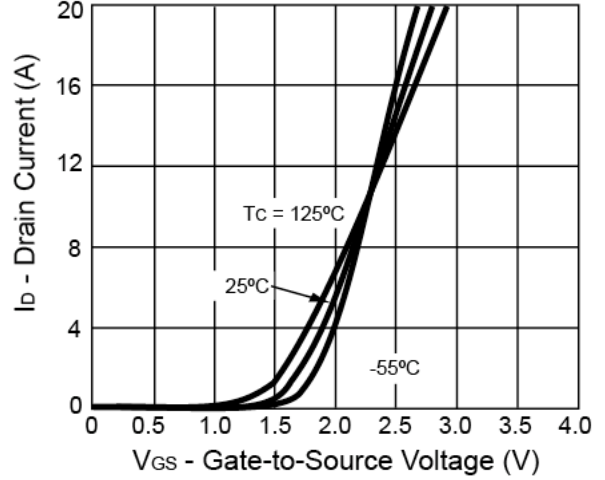
Switchin Waveforms

Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

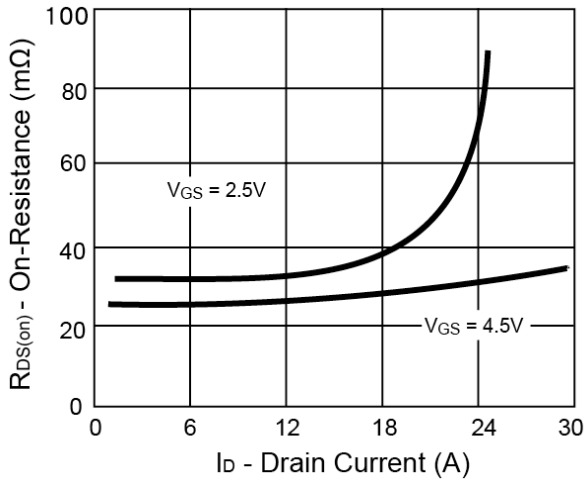
Output Characteristics



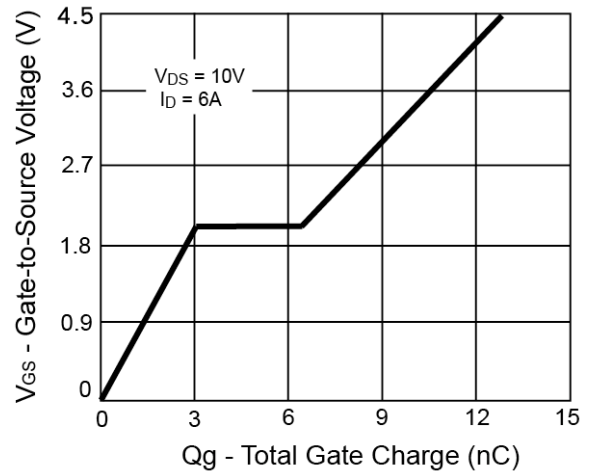
Transfer Characteristics



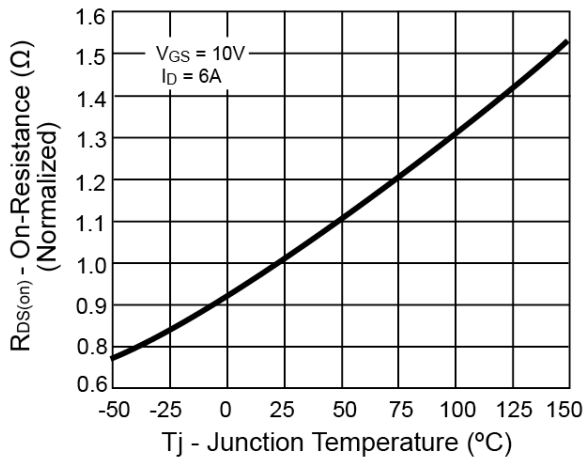
On-Resistance vs. Drain Current



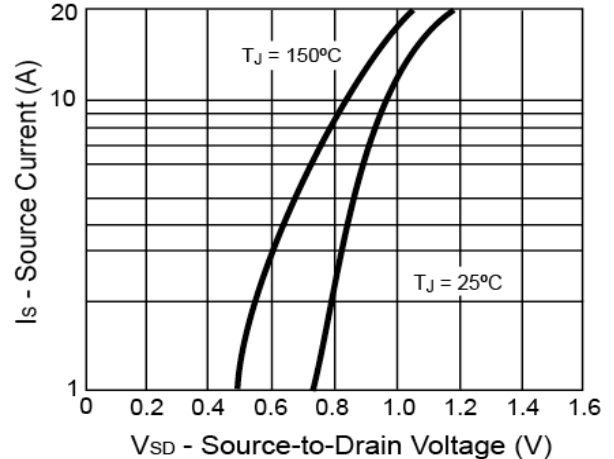
Gate Charge



On-Resistance vs. Junction Temperature

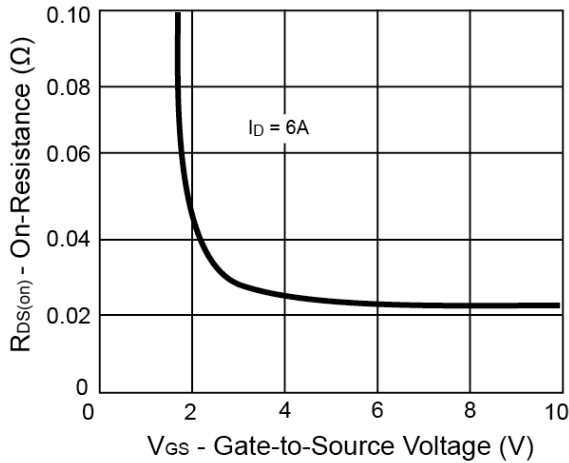


Source-Drain Diode Forward Voltage

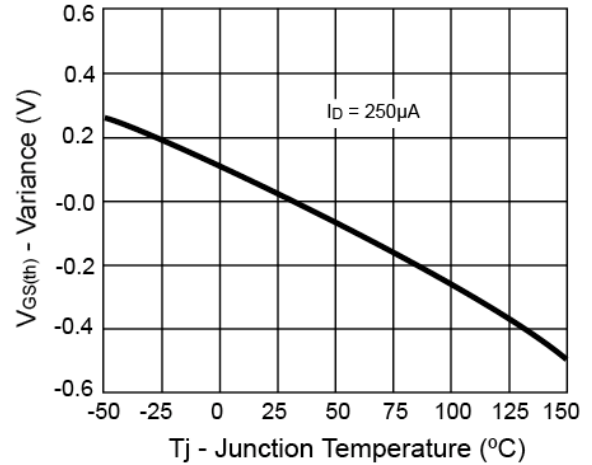


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

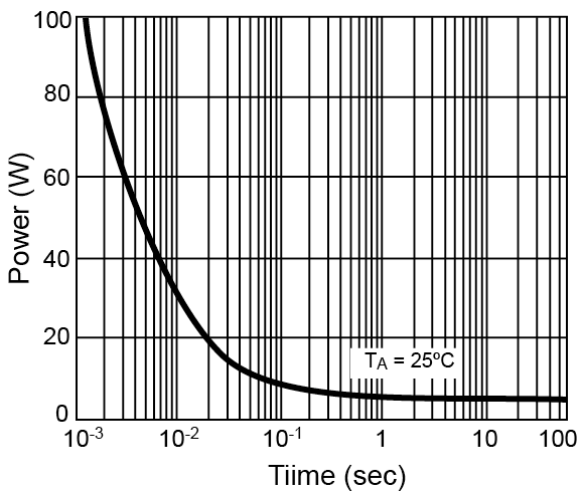
On-Resistance vs. Gate-Source Voltage



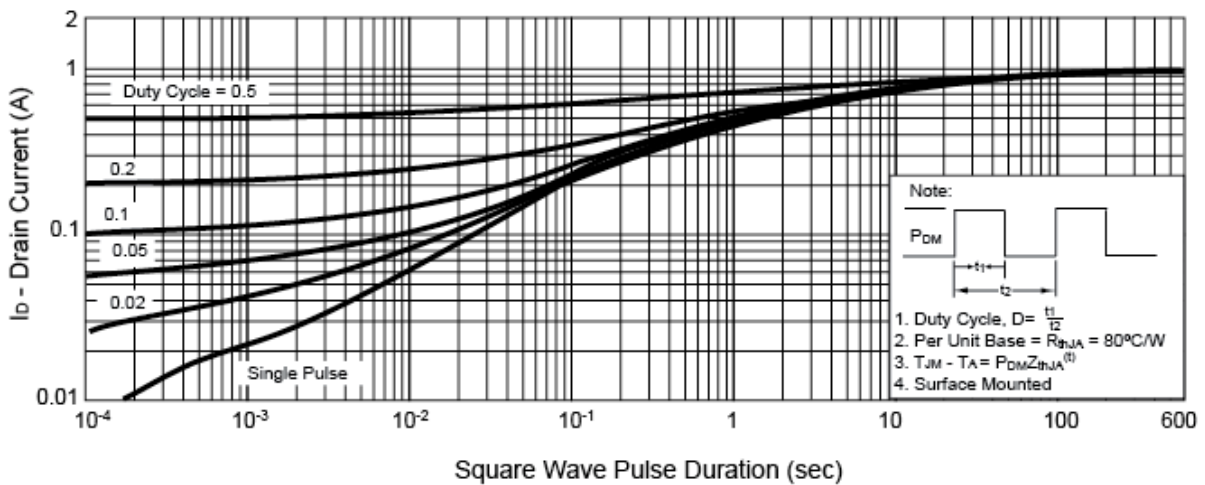
Threshold Voltage



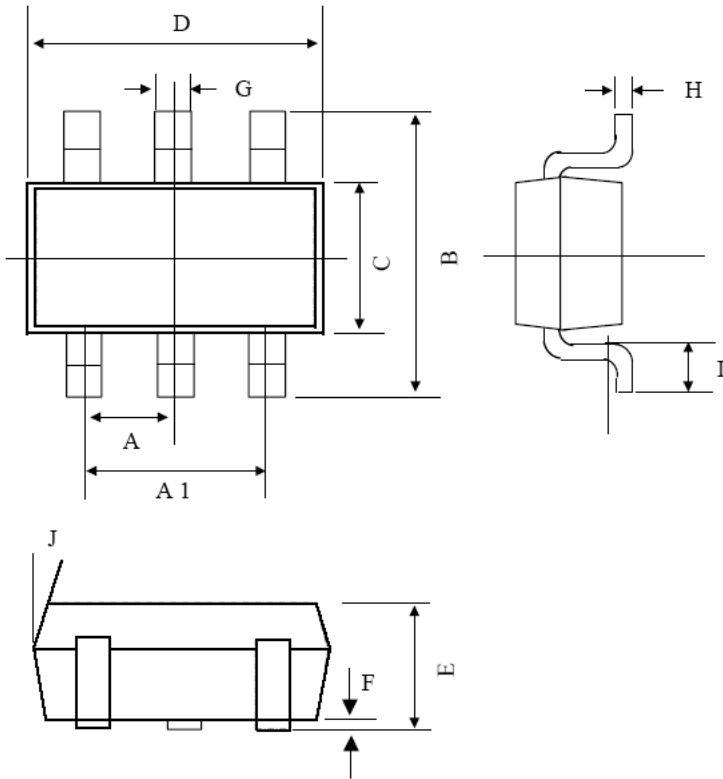
Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

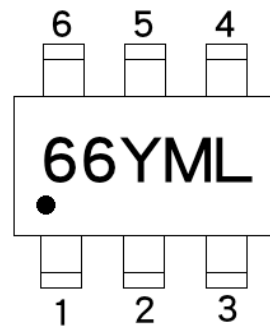


SOT-26 Mechanical Drawing



SOT-26 DIMENSION						
DIM	MILLIMETERS			INCHES		
	MIN	TYP	MAX	MIN	TYP	MAX
A	0.95 BSC			0.0374 BSC		
A1	1.9 BSC			0.0748 BSC		
B	2.60	2.80	3.00	0.1024	0.1102	0.1181
C	1.40	1.50	1.70	0.0551	0.0591	0.0669
D	2.80	2.90	3.10	0.1101	0.1142	0.1220
E	1.00	1.10	1.20	0.0394	0.0433	0.0472
F	0.00	--	0.10	0.00		0.0039
G	0.35	0.40	0.50	0.0138	0.0157	0.0197
H	0.10	0.15	0.20	0.0039	0.0059	0.0079
I	0.30	--	0.60	0.0118	--	0.0236
J	5°	--	10°	5°	--	10°

Marking Diagram



- 66** = Device Code
- Y** = Year Code
- M** = Month Code
(A=Jan, B=Feb, C=Mar, D=Apr, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)
- L** = Lot Code

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